

# YJ Planar Schottky Barrier Diode Die Specification

200V 12A, 98mil, Schottky barrier diode die based on silicon planar process

Part No.: PSB098H200SS-280A

## Main Products Characteristics

- Average forward current:  $I_F(AV) = 12\text{ A}$
- Maximum operating junction temperature:  $T_j = 175\text{ °C}$
- ESD rating: >2KV, per IEC61000-4-2 (Contact Discharge)
- Top metal: Ag

## Maximum Ratings

## Static Electrical Characteristics ( $T_a = 25\text{ °C}$ )

$I_F = 12\text{ A}$

Pulse Test:  $t_p = 300\text{ }\mu\text{s}$ , 2%

## Device Schematics and Outline Drawing

Die Thickness \*

Die Size \*\*

Top Metal Pad

Active Area

Top Metal

Back Metal

Note: 1 \*: Also can offer device with 8 mils thickness

2 \*\*: Cutting street width is around 1.5 mils

## Important Notice

Specification apply to die only. Actual performance may degrade when assembled.

does not guarantee device performance after assembly.

All operating parameters must be validated for each customer application by customer's technical experts.

Data sheet information is subjected to change without notice.

Recommended Storage Environment:

Store in original container, in dessicated nitrogen, with no contamination.

Shelf life for parts stored in above condition is 2 years.

If the storage is done in normal atmosphere shelf life is reduced to 6 months.